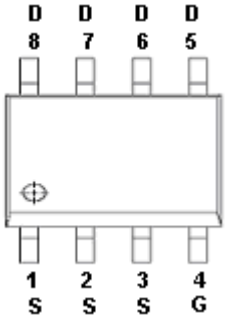
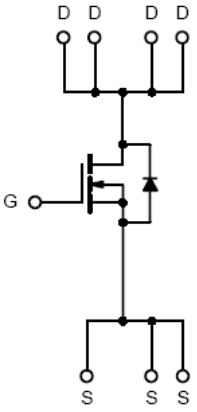
SPN4856
N-Channel Enhancement Mode MOSFET

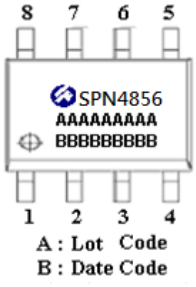
DESCRIPTION
The SPN4856 is the N-Channel logic enhancement mode power field effect transistors are produced using high cell density, DMOS trench technology. This high density process is especially tailored to minimize on-state resistance. These devices are particularly suited for low voltage application, notebook computer power management and other battery powered circuits where high-side switching is required.

APPLICATIONS
- DC/DC Converter
- Load Switch
- Synchronous Buck Converter
- Charger Adapter
- LED Lighting

FEATURES
- 40V/8A,$R_{DS(ON)}$=9mΩ@V_{GS}=10V
- 40V/4A,$R_{DS(ON)}$=13.5mΩ@V_{GS}=4.5V
- Super high density cell design for extremely low $R_{DS\ (ON)}$
- Exceptional on-resistance and maximum DC current capability
- SOP–8 package design

PIN CONFIGURATION(SOP–8)




PART MARKING


A : Lot Code
B : Date Code

SPN4856
N-Channel Enhancement Mode MOSFET

PIN DESCRIPTION

Pin	Symbol	Description
1	S	Source
2	S	Source
3	S	Source
4	G	Gate
5	D	Drain
6	D	Drain
7	D	Drain
8	D	Drain

ORDERING INFORMATION

Part Number	Package	Part Marking
SPN4856S8RGB	SOP-8	SPN4856

※ SPN4856S8RGB : 13" Tape Reel ; Pb – Free ; Halogen – Free

ABSOULTE MAXIMUM RATINGS

(T_A=25℃ Unless otherwise noted)

Parameter		Symbol	Typical	Unit
Drain-Source Voltage		V_{DSS}	40	V
Gate –Source Voltage		V_{GSS}	±20	V
Continuous Drain Current	T_A=25℃	I_D	15	A
	T_A=100℃		9.5	
Continuous Drain Current (Silicon Limited) T_A=25℃		I_D	35	A
Pulsed Drain Current		I_{DM}	60	A
Single Pulse Avalanche Energy		E_{AS}	76	mJ
Avalanche Current		I_{AS}	39	A
Power Dissipation	T_A=25℃	P_D	2.5	W
	T_A=70℃		1.4	
Operating Junction Temperature		T_J	-55/150	℃
Storage Temperature Range		T_{STG}	-55/150	℃
Thermal Resistance-Junction to Ambient		$R_{\theta JA}$	50	℃/W

SPN4856
N-Channel Enhancement Mode MOSFET

ELECTRICAL CHARACTERISTICS

(T_A=25℃ Unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V,I_D=250uA	40			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=250uA	1.0		2.5	
Gate Leakage Current	I_{GSS}	V_{DS}=0V,V_{GS}=±20V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=40V,V_{GS}=0V, T_J=25℃			1	uA
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=10V,I_D=8A			9.5	mΩ
		V_{GS}=4.5V,I_D=4A			13.5	
Forward Transconductance	gfs	V_{DS}=10V,I_D=2A		13		S
Diode Forward Voltage	V_{SD}	I_S=13.3A,V_{GS} =0V			1.5	V
Dynamic						
Total Gate Charge	Q_g	V_{DS}=20V, V_{GS}=10V I_D=8A		20		nC
Gate-Source Charge	Q_{gs}			2.8		
Gate-Drain Charge	Q_{gd}			5		
Input Capacitance	C_{iss}	V_{DS}=25V, V_{GS}=0V f=1MHz		1250		pF
Output Capacitance	C_{oss}			132		
Reverse Transfer Capacitance	C_{rss}			55		
Turn-On Time	$t_{d(on)}$	V_{DD}=15V, I_D=1A,V_{GS}=10V R_G=3.3Ω		13.2		nS
	t_r			2.2		
Turn-Off Time	$t_{d(off)}$			72		
	t_f			4.5		
Gate resistance	R_g	V_{GS}=0V,V_{DS}=0V, f=1MHz		2.2		Ω

Note :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. V_{DD}=25V, V_{GS}=10V, L=0.1mH , I_{AS}=39A , R_G=25Ω , Starting T_J=25℃
3. The data tested by pulsed, pulse width ≦300us, duty cycle ≦2%.
4. Essentially independent of operating temperature.

TYPICAL CHARACTERISTICS

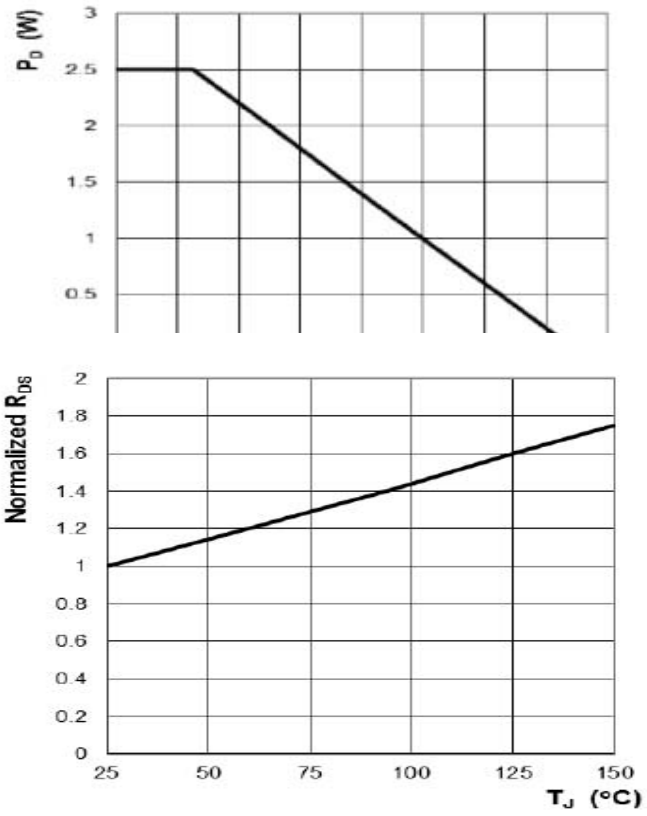


Figure 3: Normalized $R_{DS(ON)}$ vs. T_J

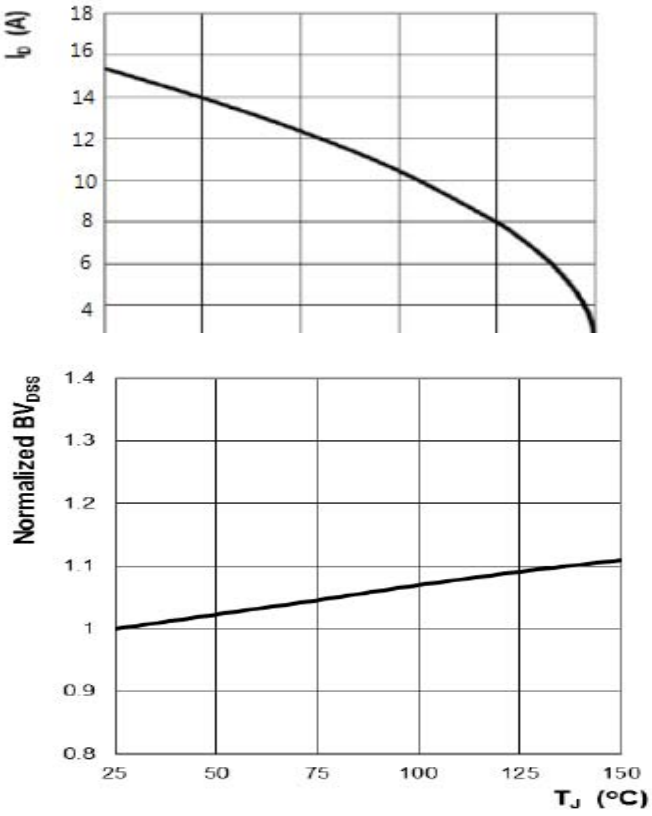


Figure 4: Normalized BV_{DSS} vs. T_J

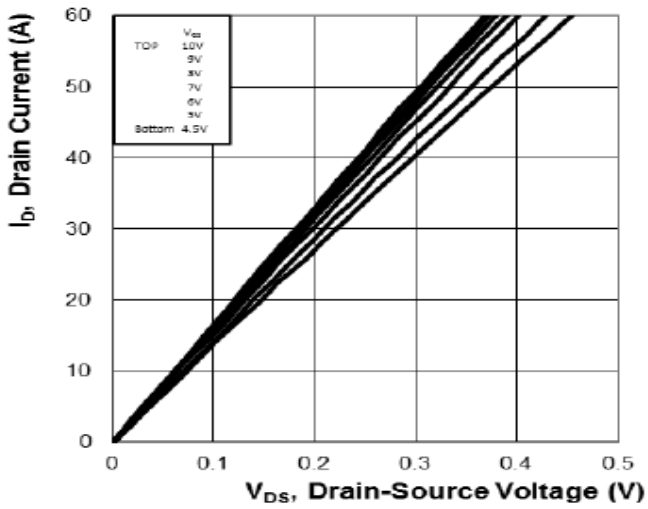


Figure 5: On-Region Characteristics

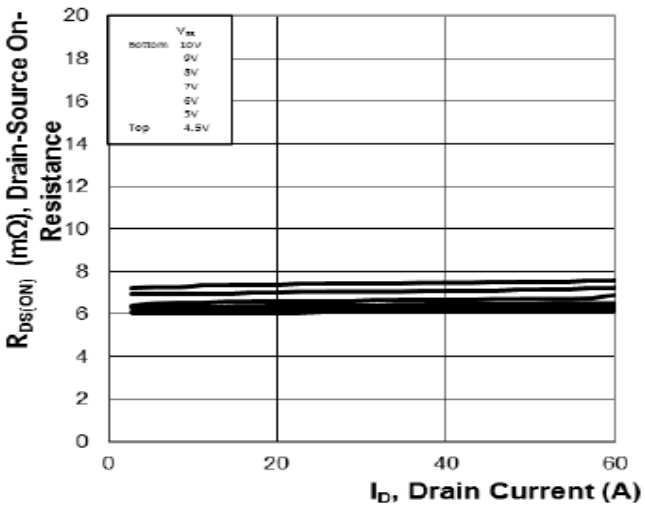


Figure 6: Typ. R_{DS} Variation vs. I_D and V_{GS}

TYPICAL CHARACTERISTICS

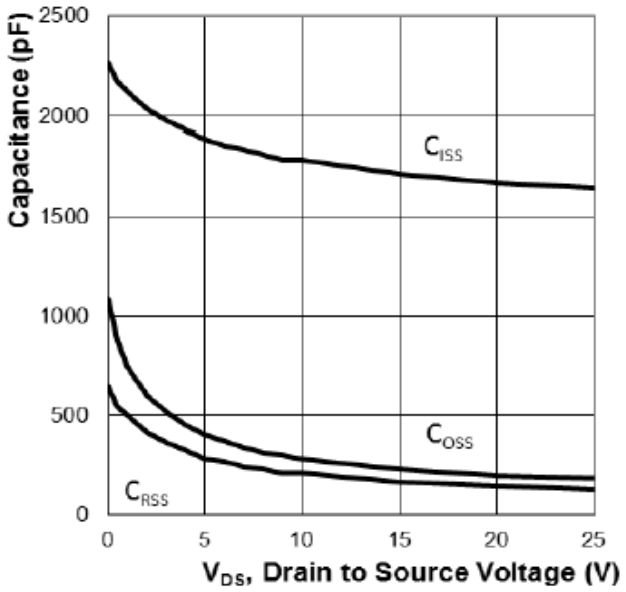


Figure 7: Typ. Capacitance Characteristics

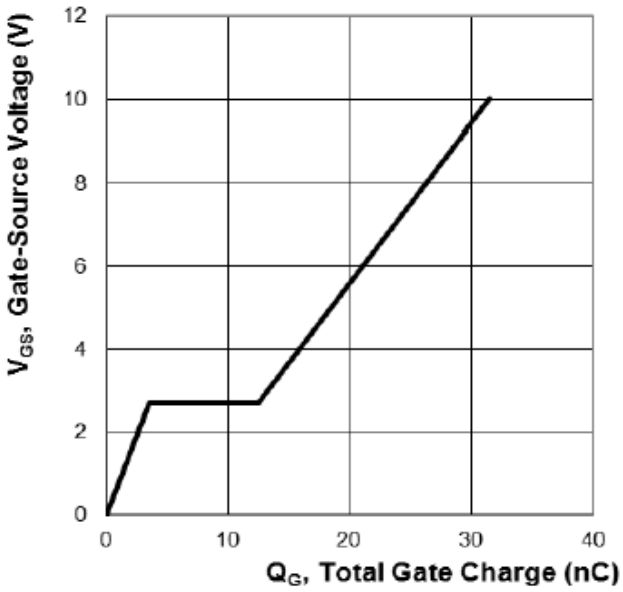


Figure 8: Typ. Gate Charge Characteristics

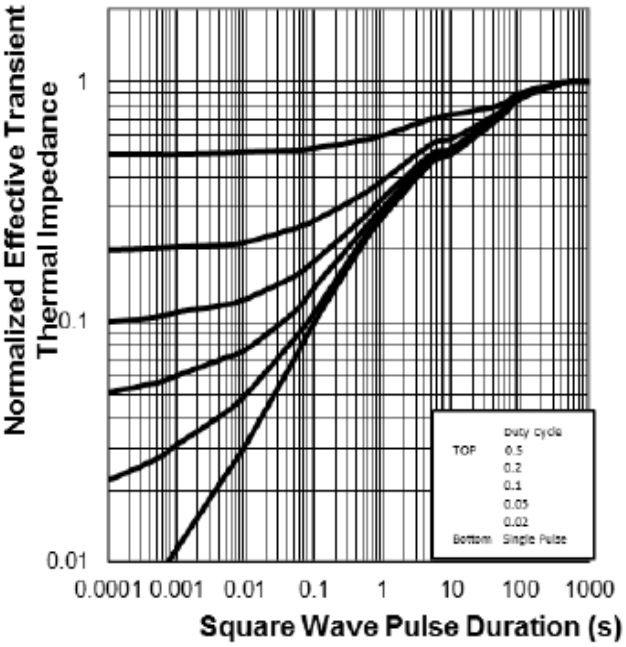


Figure 9: Normalized Thermal Transient Impedance, Junction-to-Case

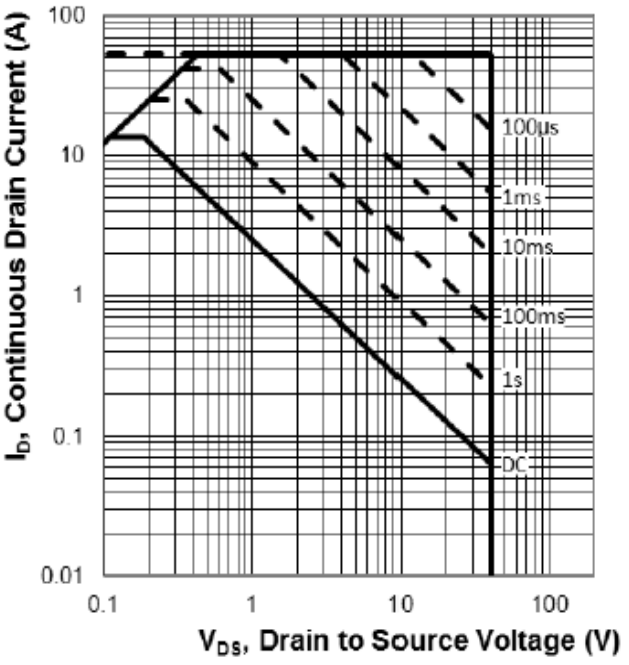


Figure 10: Maximum Safe Operation Area

SYNC Power Corporation
7F-2, No.3-1, Park Street
NanKang District (NKSP), Taipei, Taiwan 115
Phone: 886-2-2655-8178
Fax: 886-2-2655-8468
©http://www.syncpower.com